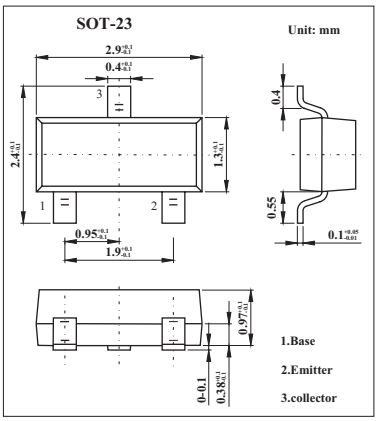
PNP Transistors

KST8550



Features

- Collector Current: I_C=-1.5A

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-1.5	A
Collector Power Dissipation	P_C	0.3	W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C=-100μA, I_E=0	-40			V
Collector-emitter breakdown voltage	V_{CEO}	I_C=-1mA, I_B=0	-25			V
Emitter-base breakdown voltage	V_{EBO}	I_E=-100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-40V, I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-20V, I_B=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-1V, I_C=-100mA	120		400	
		V_{CE}=-1V, I_C=-800mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-800mA, I_B=-80mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-800mA, I_B=-80mA			-1.2	V
Base-emitter on voltage	$V_{BE(on)}$	I_C=-1V,V_{CE}=-10mA			-1	V
Base-emitter positive favor voltage	V_{BEF}	I_B=-1A			-1.55	V
output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz			20	pF
Transition frequency	f_T	V_{CE}= -10V, I_C= -50mA,f=30MHz	100			MHz

h_{FE} Classification

Marking	Y2		
Rank	L	H	J
hFE	120～200	200～350	300～400

KST8550

■Typical Characteristics

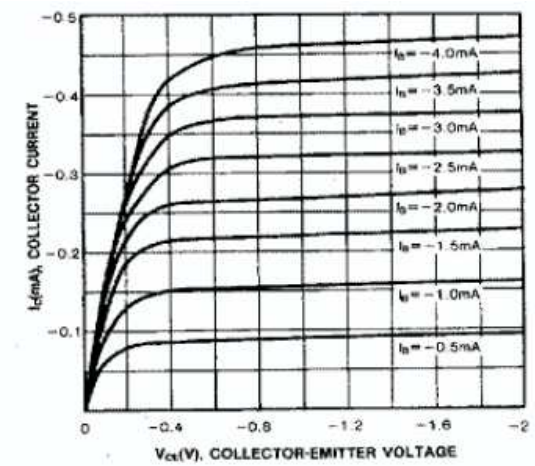


Fig.1 Static Characteristic

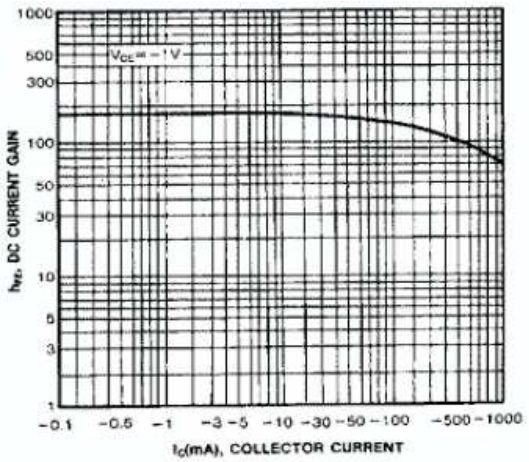


Fig.2 DC Current Gain

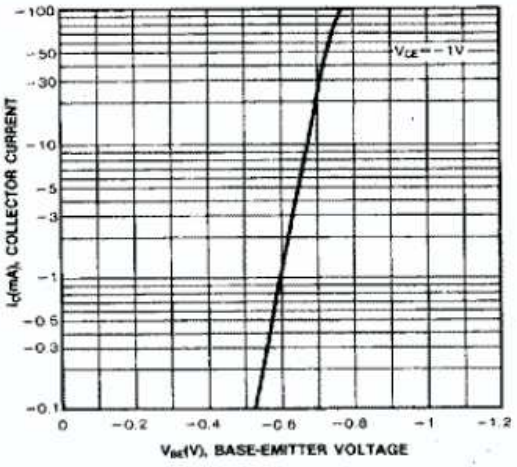


Fig.3 Base Emitter ON Voltage

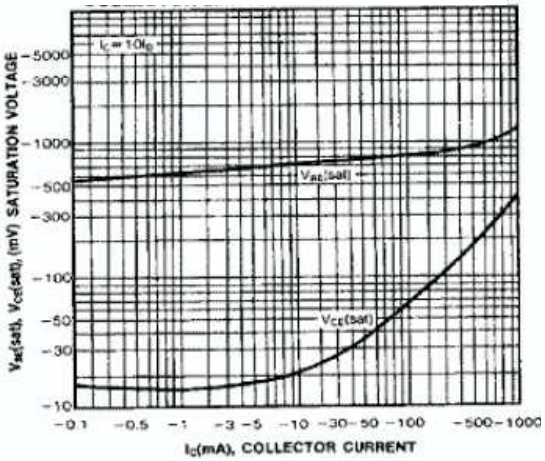


Fig.4 Base Emitter Saturation Voltage
Collector Emitter Saturation Voltage

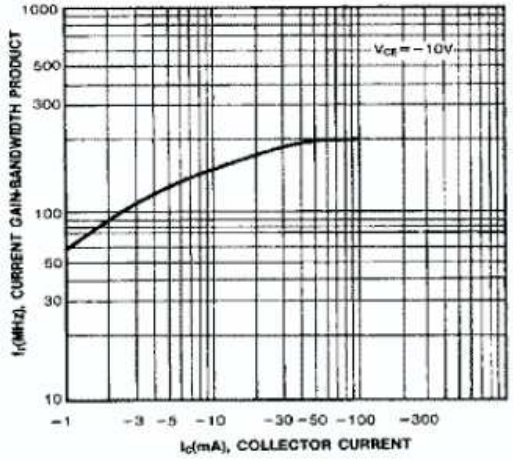


Fig.5 Current Gain Bandwidth Product

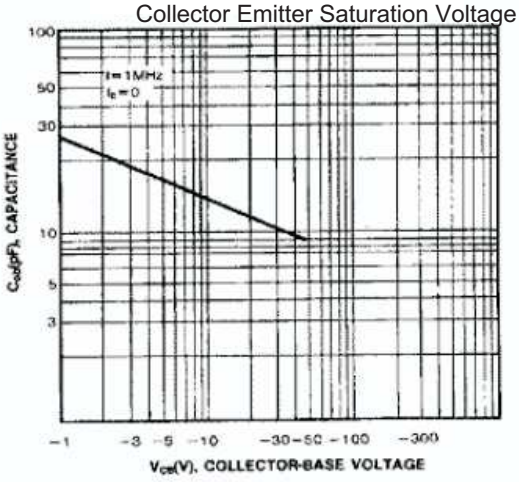


Fig.6 Collector Output Capacitance